

WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:
a fuse circuit, which comprises a first conductive region and a second conductive region, wherein
the first conductive region has a multi-layered structure, and
the second conductive region has a less layered structure than the first conductive region.
2. A semiconductor device according to claim 1, wherein
the second conductive region is formed to have a single layer structure.
3. A semiconductor device according to claim 2, wherein
the second conductive region is formed as an upper most layer.
4. A semiconductor device according to claim 3, wherein
no passivation layer is formed over the second conductive region.
5. A semiconductor device according to claim 1, comprising:
a plurality of the fuse circuits, which are arranged so that the second conductive regions are not located adjacent one another.
6. A semiconductor device according to claim 1, wherein

the first and second conductive regions form a conductive line, a length of the second conductive region along the conductive line being formed not to be larger than a double of a width of the conductive line.

7. A semiconductor device according to claim 1, wherein the fuse circuit is provided with through holes in the first conductive region to connect the layers to each other.

8. A semiconductor device according to claim 7, wherein the fuse circuit further comprises a couple of electrodes to which a predetermined voltage is applied between them in order to disconnect the second conductive region.

9. A semiconductor device according to claim 1, wherein a laser beam is applied to the second conductive region in order to disconnect it.

10. A semiconductor device according to claim 1, wherein the fuse circuit is applicable to one selected from a redundant fuse in a semiconductor device; a fuse adjusting a resistance and/or capacity in a semiconductor device; a fuse used for switching logic circuits in a semiconductor device; and a fuse used for adjusting an output level of signal in a semiconductor device.

11. A fuse circuit, comprising:
a first conductive region having a multi-layered structure; and
a second conductive region having a less layered structure
than the first conductive region.
12. A fuse circuit according to claim 11, wherein
the second conductive region is formed to have a single layer
structure.
13. A fuse circuit according to claim 12, wherein
the second conductive region is formed as an upper most layer.
14. A fuse circuit according to claim 13, wherein
no passivation layer is formed over the second conductive
region.
15. A fuse circuit according to claim 11, wherein
the first and second conductive regions form a conductive line,
and
the fuse circuit comprises a plurality of the conductive lines,
which are arranged so that the second conductive regions are not
located adjacent one another.
16. A fuse circuit according to claim 11, wherein
in each of the conductive lines, a length of the second

conductive region is formed not to be larger than a double of a width of the conductive line.

17. A fuse circuit according to claim 11, wherein
through holes are provided in the first conductive region to connect the layers to each other.

18. A fuse circuit according to claim 17 further comprising:
a couple of electrodes to which a predetermined voltage is applied between them in order to disconnect the second conductive region.

19. A fuse circuit according to claim 11, wherein
a laser beam is applied to the second conductive region in order to disconnect it.

20. A fuse circuit according to claim 11, wherein
the fuse circuit is applicable to one selected from a redundant fuse in a semiconductor device; a fuse adjusting a resistance and/or capacity in a semiconductor device; a fuse used for switching logic circuits in a semiconductor device; and a fuse used for adjusting an output level of signal in a semiconductor device.